



#### 60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C (Note 9)
60V	$3.65 \text{m}\Omega @ V_{GS} = 10V$	100A

### **Features**

- Low Input Capacitance
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Description and Applications**

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

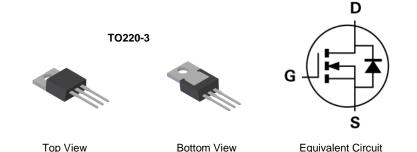
### **Mechanical Data**

- Case: TO220-3
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)

Top View

Pin Out Configuration

- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)



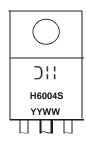
### Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH6004SCT	TO220-3	50 Pieces/Tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



Dili=Manufacturer's Marking
H6004S = Product Type Marking Code
YYWW = Date Code Marking
YY or YY = Last Digit of Year (ex: 15 = 2015)
WW or WW = Week Code (01 to 53)



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	$V_{DSS}$	60	V	
Gate-Source Voltage	$V_{GSS}$	±20	V	
Continuous Drain Current (Note 6)	T <sub>C</sub> = +25°C (Note 9)	ID	100	А
,	T <sub>C</sub> = +100°C	J	100	
Maximum Continuous Body Diode Forward Current (Note 6)	T <sub>C</sub> = +25°C	I <sub>S</sub>	100	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	180	Α	
Avalanche Current, L=0.2mH	I <sub>AS</sub>	45	Α	
Avalanche Energy, L=0.2mH	E <sub>AS</sub>	200	mJ	

### **Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25$ °C	$P_{D}$	2.8	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	52.8	°C/W
Total Power Dissipation (Note 6)	$T_C = +25^{\circ}C$	$P_D$	136	W
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	1.1	°C/W
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +175	°C

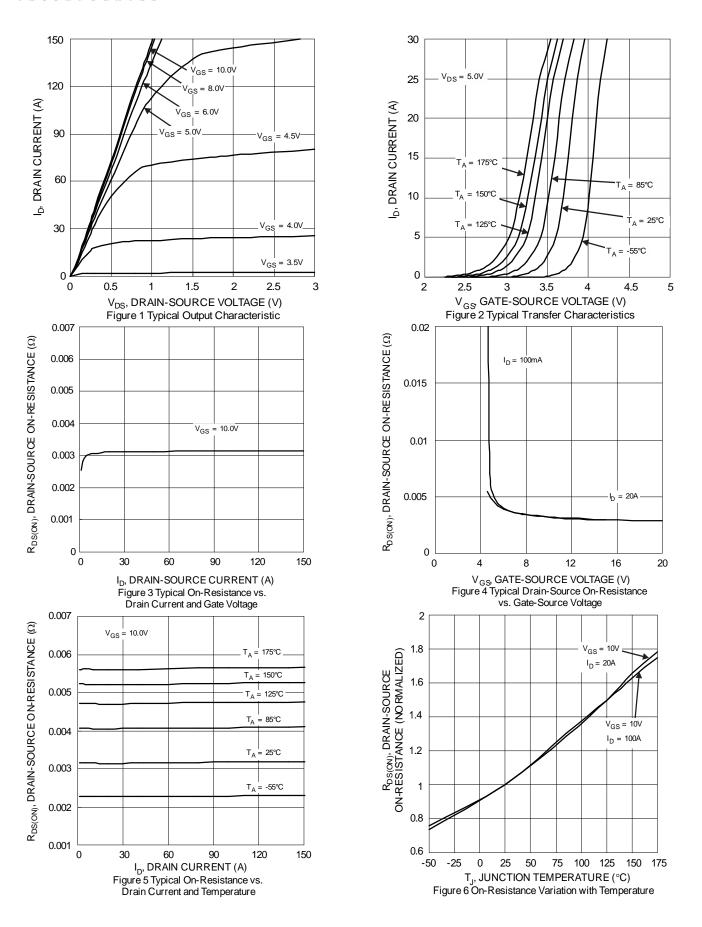
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	1	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	_	4	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	3.1	3.65	mΩ	$V_{GS} = 10V, I_{D} = 100A$	
Diode Forward Voltage	$V_{SD}$	_		1.3	V	$V_{GS} = 0V, I_{S} = 100A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>ISS</sub>	_	4,556	_		$V_{DS} = 30V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Output Capacitance	Coss	_	1,383	1	pF		
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	105	1			
Gate Resistance	R <sub>G</sub>	_	0.7	1	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	$Q_{G}$	_	95.4	1		V <sub>DD</sub> = 30V, I <sub>D</sub> = 90A, V <sub>GS</sub> = 10V	
Gate-Source Charge	$Q_GS$	_	21.6	1	nC		
Gate-Drain Charge	$Q_{GD}$	_	20.4	_		VGS = 10V	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	14.3	1			
Turn-On Rise Time	t <sub>R</sub>	_	99.1	1	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 90A, R_{G} = 3.5\Omega$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	40	1	115		
Turn-Off Fall Time	t <sub>F</sub>	_	17.6	_			
Reverse Recovery Time	t <sub>RR</sub>		50.5		ns	I 49A_di/dt _ 100A/ug	
Reverse Recovery Charge	Q <sub>RR</sub>	_	80.8		nC	$I_F = 48A$ , di/dt = 100A/ $\mu$ s	

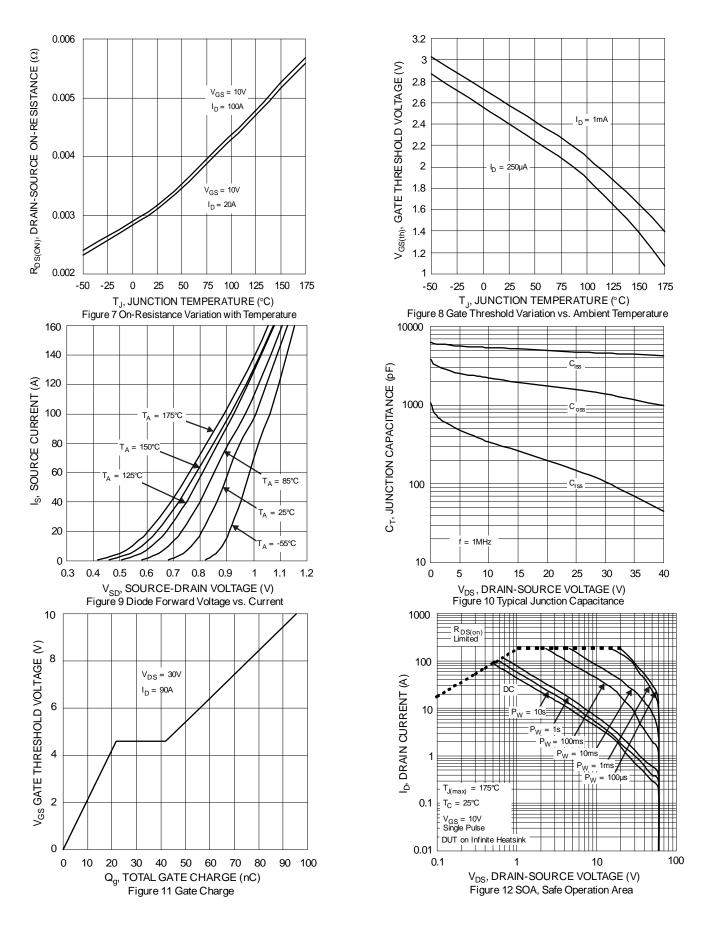
Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on infinite heat sink.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.
- 9. Package limited.

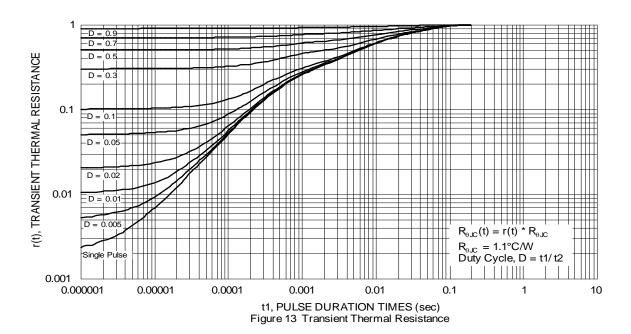










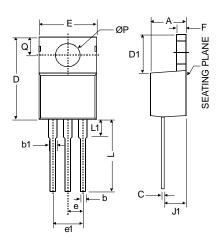




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### TO220-3



TO220-3				
Dim	Min	Max		
Α	3.55	4.85		
p	0.51	1.14		
b1	1.14	1.78		
C	0.31	1.14		
D	14.20	16.50		
D1	5.84	6.86		
Е	9.70	10.70		
е	2.79	2.99		
e1	4.83	5.33		
F	0.51	1.40		
J1	2.03	2.92		
L	12.72	14.72		
L1	3.66	6.35		
Р	3.53	4.09		
Ø	2.54	3.43		
All Dimensions in mm				



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